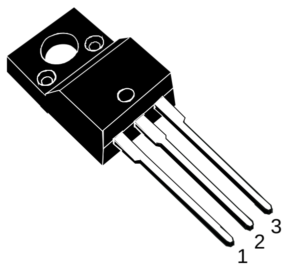
STFU15NM65N

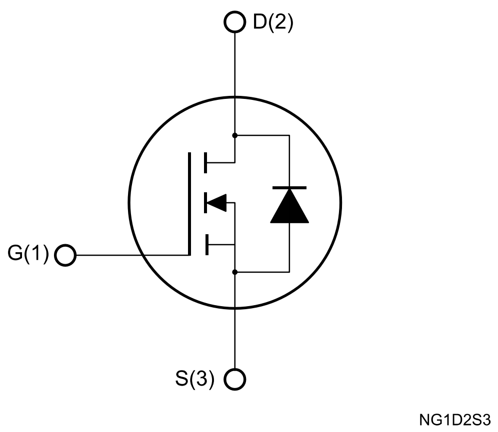
N-channel 650 V, 0.35 Ω typ., 12 A MDmesh™ II
Power MOSFET in a TO-220FP ultra narrow leads package

Datasheet - production data



TO-220FP
ultra narrow leads

Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max	I_D
STFU15NM65N	650 V	0.38 Ω	12 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packaging
STFU15NM65N	15NM65N	TO-220FP ultra narrow leads	Tube

This is information on a product in full production.

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain source voltage	650	V
V_{GS}	Gate source voltage	± 25	V
I_D	Drain current (continuous) at T_C = 25 °C	12[(1)]	A
	Drain current (continuous) at T_C = 100 °C	7.56	
I_{DM}[(2)]	Drain current (pulsed)	48	A
P_{TOT}	Total dissipation at T_C = 25 °C	30	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T_C = 25 °C)	2500	V
dv/dt [(3)]	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Operating junction temperature		

Notes:

(1)Limited by maximum junction temperature.

(2)Pulse width limited by safe operating area.

(3)I_{SD} ≤ 12 A, di/dt ≤ 400 A/μs; V_{DSpeak} ≤ $V_{(BR)DSS}$, V_{DD} = 80% $V_{(BR)DSS}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	4.17	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5	

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	3	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25°C, I_D = I_{AR}; V_{DD} = 50 V)	187	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	650			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 650 V			1	µA
		V_{DS} = 650 V, T_C = 125 °C			100	µA
I_{GSS}	Gate-body leakage current (V_{DS} = 0)	V_{GS} = ± 25 V			±100	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 6 A		0.35	0.38	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0 V	-	983	-	pF
C_{oss}	Output capacitance		-	57	-	
C_{rss}	Reverse transfer capacitance		-	4.5	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 520 V, V_{GS} = 0 V	-	146	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	4.9	-	Ω
Q_g	Total gate charge	V_{DD} = 520 V, I_D = 12 A, V_{GS} = 10 V	-	33.3	-	nC
Q_{gs}	Gate-source charge		-	5.7	-	
Q_{gd}	Gate-drain charge		-	17	-	

Notes:

(1) $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 325 V, I_D = 6 A, R_G = 4.7 Ω, V_{GS} = 10 V	-	55.5	-	ns
t_r	Rise time		-	8.5	-	
$t_{d(off)}$	Turn-off delay time		-	14	-	
t_f	Fall time		-	11.4	-	

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		12	A
I_{SDM} (1)	Source-drain current (pulsed)		-		48	A
V_{SD} (2)	Forward on voltage	I_{SD} = 12 A, V_{GS} = 0 V	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 12 A, di/dt = 100 A/µs, V_{DD} = 60 V	-	428		ns
Q_{rr}	Reverse recovery charge		-	4.7		µC
I_{RRM}	Reverse recovery current		-	21.5		A
t_{rr}	Reverse recovery time	I_{SD} = 12 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C	-	570		ns
Q_{rr}	Reverse recovery charge		-	6.2		µC
I_{RRM}	Reverse recovery current		-	22		A

Notes:

(1)Pulse width limited by safe operating area.

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

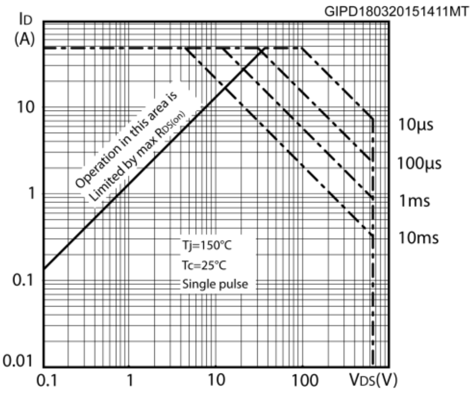


Figure 3: Thermal impedance

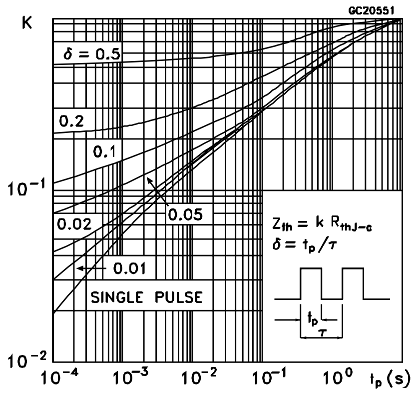


Figure 4: Output characteristics

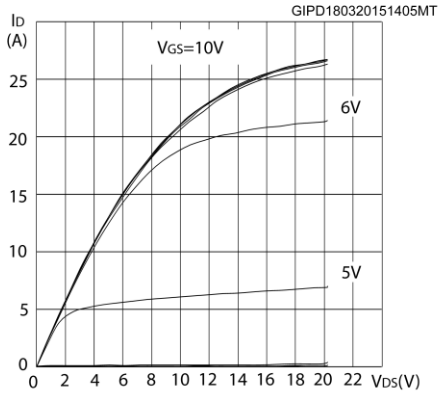


Figure 5: Transfer characteristics

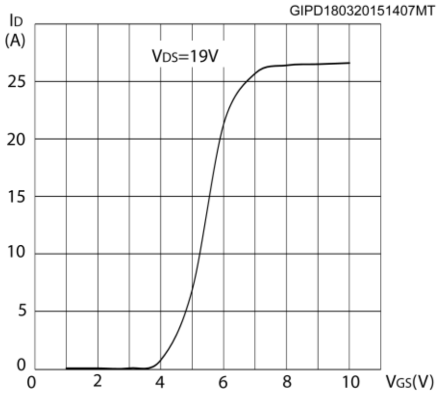


Figure 6: Static drain-source on-resistance

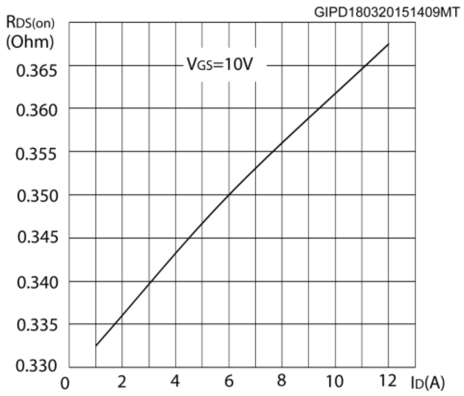


Figure 7: Gate charge vs gate-source voltage

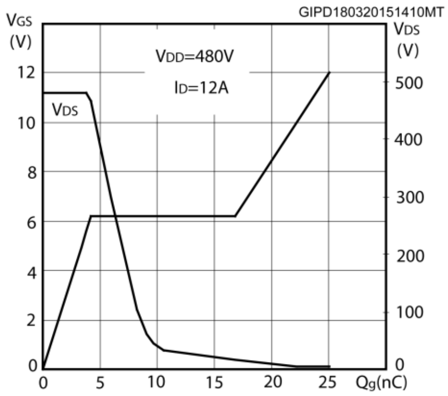


Figure 8: Capacitance variations

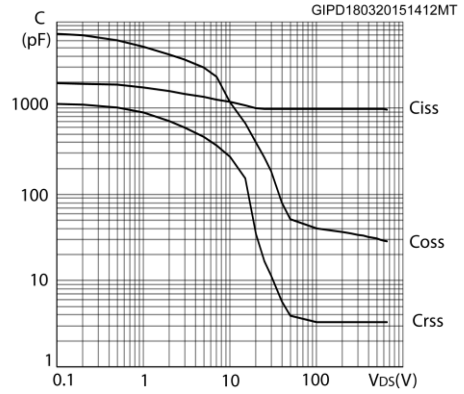


Figure 9: Normalized gate threshold voltage vs temperature

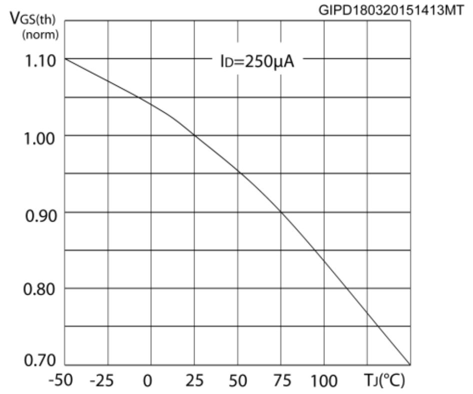


Figure 10: Normalized on-resistance vs temperature

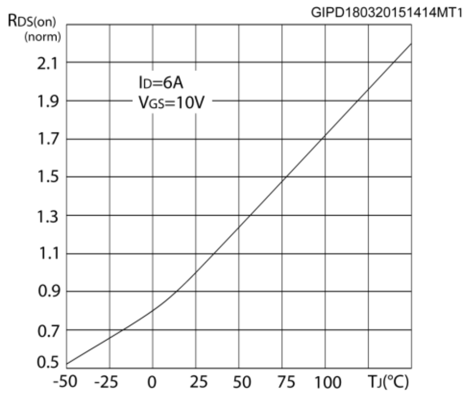


Figure 11: Source-drain diode forward characteristics

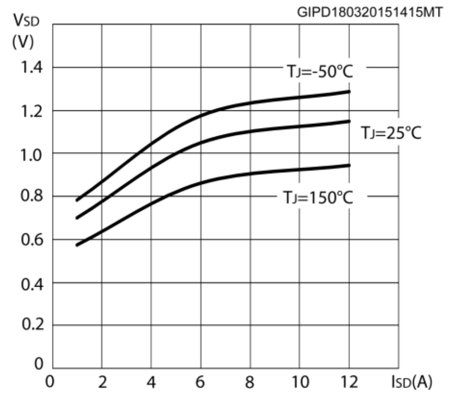


Figure 12: Normalized $V_{(BR)DSS}$ vs temperature

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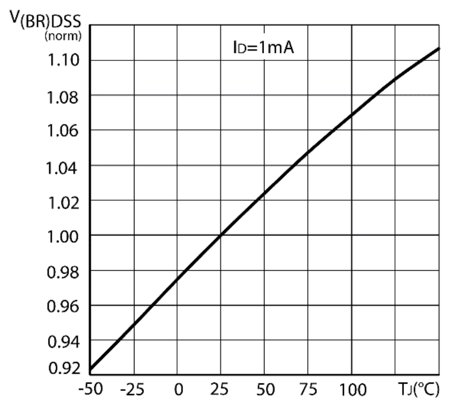


3 Test circuit

Figure 13: Test circuit for resistive load switching times

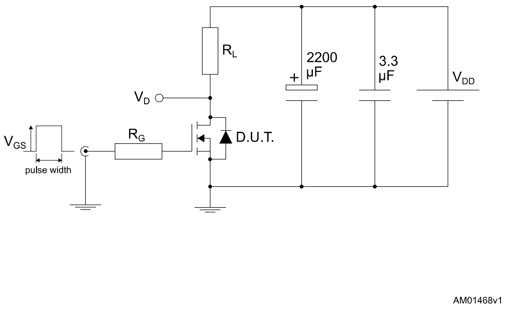


Figure 14: Test circuit for gate charge behavior

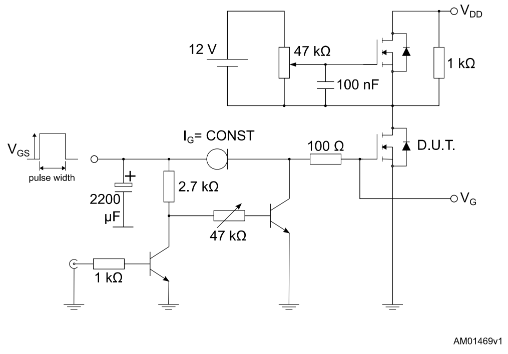


Figure 15: Test circuit for inductive load switching and diode recovery times

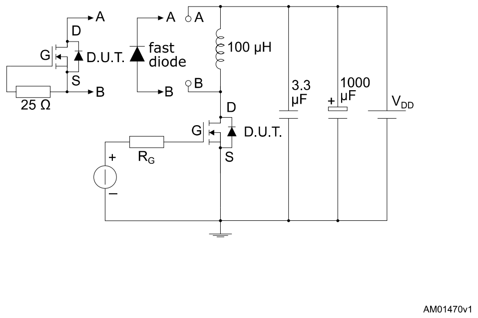


Figure 16: Unclamped inductive load test circuit

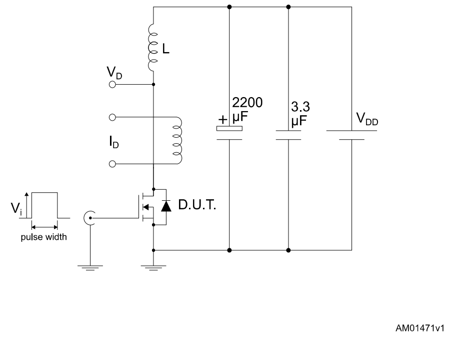


Figure 17: Unclamped inductive waveform

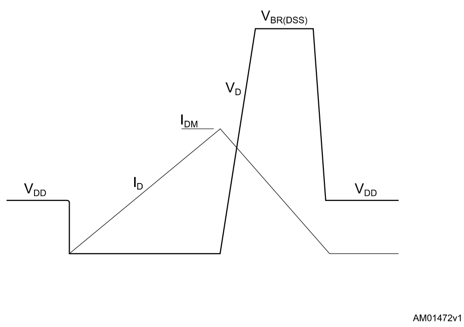
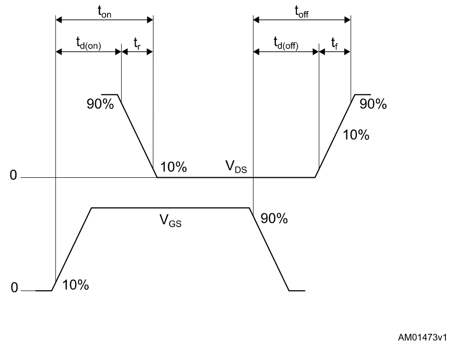


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 TO-220FP ultra narrow leads package information

Figure 19: TO-220FP ultra narrow leads package outline

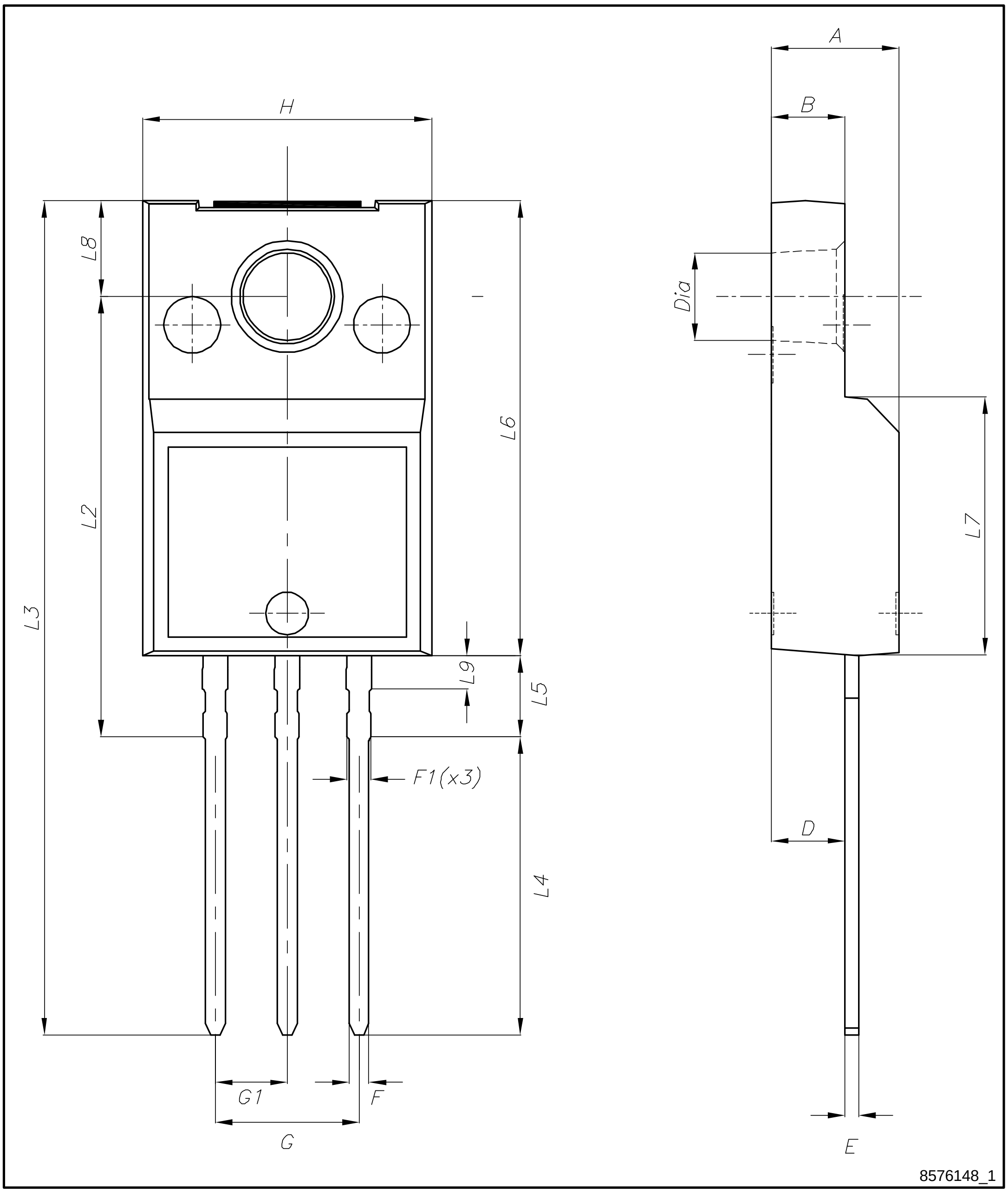


Table 9: TO-220FP ultra narrow leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.60
F	0.65		0.75
F1	-		0.90
G	4.95		5.20
G1	2.40	2.54	2.70
H	10.00		10.40
L2	15.10		15.90
L3	28.50		30.50
L4	10.20		11.00
L5	2.50		3.10
L6	15.60		16.40
L7	9.00		9.30
L8	3.20		3.60
L9	-		1.30
Dia.	3.00		3.20

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
16-Mar-2015	1	Initial release
09-Sep-2015	2	Datasheet status promoted from preliminary to production data.

IMPORTANT NOTICE – PLEASE READ CAREFULLY